

Abstract Submitted  
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**Engineered** **Uni-**  
**form Conduction Fronts in Memristive/Memcapacitive Systems** PATRICK  
MICKEL, CONRAD JAMES, Sandia National Laboratories — We introduce here a  
novel “memristor” design enabling the uniform propagation of the conduction front  
within the device, improving performance as well as device-to-device consistency.  
Typically, resistive switching in memristors occurs due to the localized formation of  
conductive filaments. Electric fields are magnified at filament tips (due to decreased  
separation,  $E = V/d$ ), amplifying growth rates for select filaments and producing a  
localized and highly non-uniform conduction front. However, we show that by incor-  
porating specifically spaced layers with alternating ionic mobilities the electric field  
magnification can be counterbalanced, resulting in a uniform conduction front. The  
uniform conduction front lowers device-to-device variability, improves analog tuning  
and significantly amplifies the memcapacitive properties of the device. These multi-  
layered engineered nanostructures have potential applications in multi-bit memory  
storage and neuromorphic computing architectures.

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